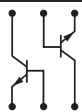


CMLT5551

**SURFACE MOUNT  
DUAL NPN SMALL SIGNAL  
HIGH VOLTAGE  
SILICON SWITCHING TRANSISTORS**

PICOmini™



**SOT-563 CASE**

**Central**  
Semiconductor Corp.

[www.centrasemi.com](http://www.centrasemi.com)

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLT5551 consists of two individual, isolated NPN silicon transistors, manufactured by the epitaxial planar process and epoxy molded in an SOT-563 surface mount package. This PICOmini™ devices has been designed for high voltage amplifier applications.

**MARKING CODE: 5C5**

**MAXIMUM RATINGS:** ( $T_A=25^\circ\text{C}$ )

Collector-Base Voltage  
Collector-Emitter Voltage  
Emitter-Base Voltage  
Continuous Collector Current  
Power Dissipation  
Operating and Storage Junction Temperature  
Thermal Resistance

**SYMBOL**

$V_{CBO}$  180  
 $V_{CEO}$  160  
 $V_{EBO}$  6.0  
 $I_C$  600  
 $P_D$  350  
 $T_J, T_{stg}$  -65 to +150  
 $\theta_{JA}$  357

**UNITS**

V  
V  
V  
mA  
mW  
 $^\circ\text{C}$   
 $^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS PER TRANSISTOR:** ( $T_A=25^\circ\text{C}$  unless otherwise noted)

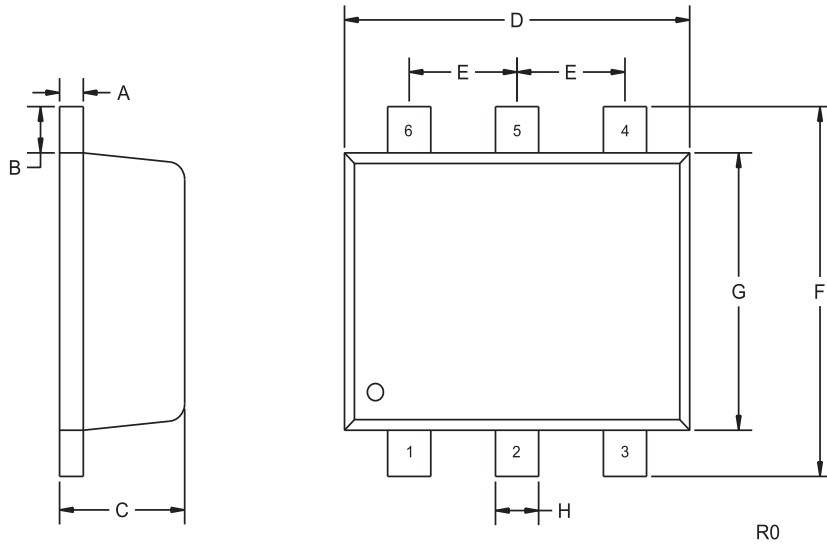
SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
$I_{CBO}$	$V_{CB}=120\text{V}$		50	nA
$I_{CBO}$	$V_{CB}=120\text{V}, T_A=100^\circ\text{C}$		50	$\mu\text{A}$
$BV_{CBO}$	$I_C=100\mu\text{A}$	180		V
$BV_{CEO}$	$I_C=1.0\text{mA}$	160		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	6.0		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		0.15	V
$V_{CE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		0.20	V
$V_{BE(SAT)}$	$I_C=10\text{mA}, I_B=1.0\text{mA}$		1.00	V
$V_{BE(SAT)}$	$I_C=50\text{mA}, I_B=5.0\text{mA}$		1.00	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	80		
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	80	250	
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=50\text{mA}$	30		
$f_T$	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	100	300	MHz
$C_{ob}$	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		6.0	pF
$h_{fe}$	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	200	
NF	$V_{CE}=5.0\text{V}, I_C=200\mu\text{A}, R_S=10\Omega,$ $f=10\text{Hz to } 15.7\text{kHz}$		8.0	dB

R1 (20-January 2010)

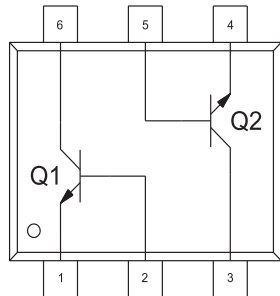
**CMLT5551**  
**SURFACE MOUNT**  
**DUAL NPN SMALL SIGNAL**  
**HIGH VOLTAGE**  
**SILICON SWITCHING TRANSISTORS**



**SOT-563 CASE - MECHANICAL OUTLINE**



**PIN CONFIGURATION**



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

**LEAD CODE:**

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q1
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q2

**MARKING CODE: 5C5**

R1 (20-January 2010)